

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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Nch 800V 2A Power MOSFET

V_{DSS}	800V
R _{DS(on)} (Max.)	4.3Ω
I _D	2A
P_{D}	36W

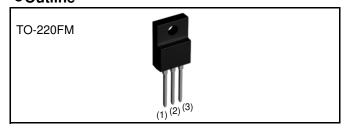
Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 30V$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

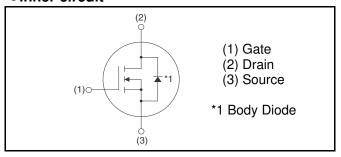
Application

Switching Power Supply

Outline



•Inner circuit



Packaging specifications

	Packaging	Bulk
	Reel size (mm)	-
Typo	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	500
	Taping code	-
	Marking	R8002ANX

•Absolute maximum ratings($T_a = 25^{\circ}C$)

Paramete	Symbol	Value	Unit	
Drain - Source voltage		V _{DSS}	800	V
Continuous drain current	$T_c = 25^{\circ}C$	I _D *1	±2	А
	T _c = 100°C	I _D *1	±1	А
Pulsed drain current	I _{D,pulse} *2	±8	А	
Gate - Source voltage		V _{GSS}	±30	V
Avalanche energy, single pulse		E _{AS} *3	0.265	mJ
Avalanche energy, repetitive		E _{AR} *4	0.212	mJ
Avalanche current		I _{AR} *3	1	Α
Power dissipation (T _c = 25°C)		P _D	36	W
Junction temperature		T _j	150	°C
Range of storage temperature		T _{stg}	-55 to +150	°C
Reverse diode dv/dt		dv/dt *5	15	V/ns

• Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 480V, I_{D} = 2A$ $T_{j} = 125^{\circ}C$	50	V/ns

●Thermal resistance

Parameter	Symbol	Values			Unit
Farameter	Symbol	Min.	Тур.	Max.	UTIIL
Thermal resistance, junction - case	R_{thJC}	-	-	3.41	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	70	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

$\bullet \textbf{Electrical characteristics}(T_a = 25^{\circ}C)$

Parameter	Cumbal	Conditions	Values			Unit
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	800	-	ı	V
Drain - Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS} = 0V$, $I_D = 2A$	-	900	-	٧
Zero gate voltage drain current	I _{DSS}	V_{DS} = 800V, V_{GS} = 0V T_j = 25°C T_j = 125°C	-	0.1	100	μА
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 30V, \ V_{DS} = 0V$	-	-	±100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10V, I_{D} = 1mA$	3	-	5	V
Static drain - source on - state resistance	R _{DS(on)} *6	$V_{GS} = 10V$, $I_D = 1A$ $T_j = 25$ °C $T_j = 125$ °C	-	3.3 6.63	4.3	Ω
Gate input resistance	R_{G}	f = 1MHz, open drain	-	5.9	-	Ω

•Electrical characteristics($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
raiainetei	Symbol	Conditions	Min.	Тур.	Max.	Ullit
Transconductance	g _{fs} *6	$V_{DS} = 10V, I_{D} = 1.0A$	0.5	1	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	210	-	
Output capacitance	C _{oss}	V _{DS} = 25V	-	130	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	14	-	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0V$,	-	15.5	-	5E
Effective output capacitance, time related	C _{o(tr)}	$V_{DS} = 0V$ to $480V$	-	15.6	-	pF
Turn - on delay time	t _{d(on)} *6	$V_{DD} \simeq 400V$, $V_{GS} = 10V$	-	17	-	
Rise time	t _r *6	I _D = 1A	-	20	-	20
Turn - off delay time	t _{d(off)} *6	$R_L = 400\Omega$	-	33	66	ns
Fall time	t _f *6	$R_G = 10\Omega$	-	70	140	

•Gate Charge characteristics($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
rarameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q_g^{*6}	$V_{DD} \simeq 400V$	-	12.7	ı	
Gate - Source charge	Q _{gs} *6	$I_D = 2A$	-	2.7	-	nC
Gate - Drain charge	Q _{gd} *6	V _{GS} = 10V	-	4.3	-	
Gate plateau voltage	V _(plateau)	$V_{DD} \simeq 400V$, $I_D = 2A$	-	7.4	-	V

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw \leq 10 $\mu s,~Duty~cycle \leq$ 1%

^{*3} L $^{\simeq}$ 500 μ H, V_{DD} = 50V, R_{G} = 25 Ω , starting T_{j} = 25°C

^{*4} L $^{\sim}$ 500 μ H, V_{DD} = 50V, R_{G} = 25 Ω , starting T_{j} = 25°C, f = 10kHz

^{*5} Reference measurement circuits Fig.5-1.

^{*6} Pulsed

ullet Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	T _c = 25°C	-	1	2	А
Inverse diode direct current, pulsed	I _{SM} *2	. *2	-	-	8	А
Forward voltage	V _{SD} *6	$V_{GS} = 0V, I_{S} = 2A$	-	-	1.5	V
Reverse recovery time	t _{rr} *6		-	481	-	ns
Reverse recovery charge	Q _{rr} *6	I _S = 2A di/dt = 100A/us	-	2.5	-	μС
Peak reverse recovery current	I _{rrm} *6		-	10.5	-	Α
Peak rate of fall of reverse recovery current	di _{rr} /dt	T _j = 25°C	-	50	-	A/μs

● Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	0.486	
R _{th2}	1.31	K/W
R _{th3}	1.96	

Symbol	Value	Unit
C _{th1}	0.00095	
C _{th2}	0.0112	Ws/K
C _{th3}	0.521	

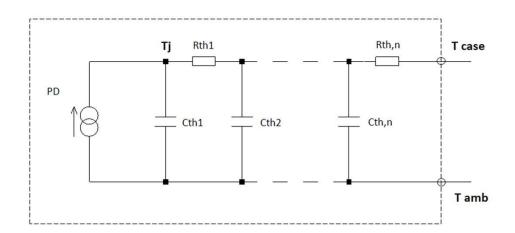
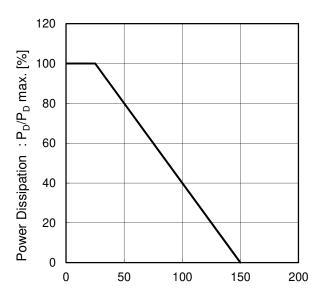
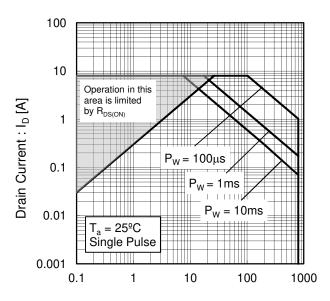


Fig.1 Power Dissipation Derating Curve



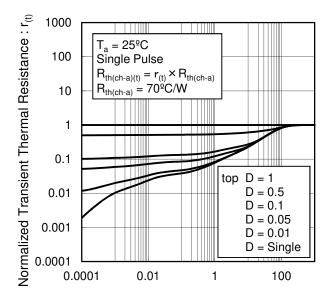
Junction Temperature : Tj [°C]

Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : V_{DS} [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



Pulse Width: P_W [s]

Fig.4 Avalanche Current vs Inductive Load

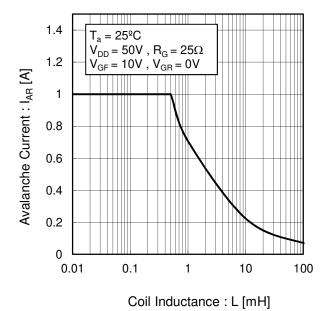
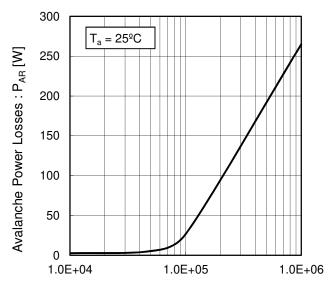


Fig.5 Avalanche Power Losses



Frequency: f [Hz]

Fig.6 Avalanche Energy Derating Curve vs Junction Temperature

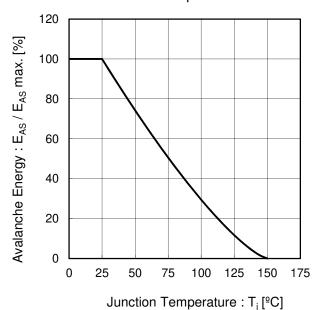


Fig.7 Typical Output Characteristics(I)

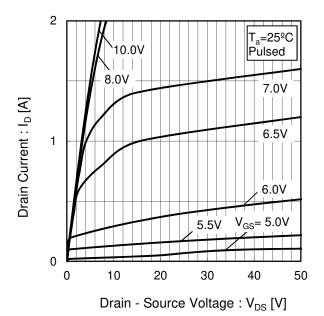


Fig.8 Typical Output Characteristics(II)

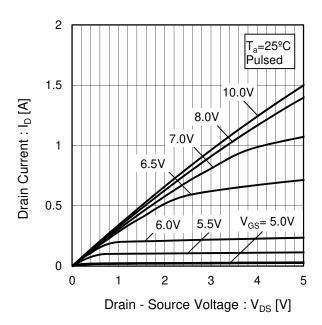


Fig.9 $T_j = 150$ °C Typical Output Characteristics(I)

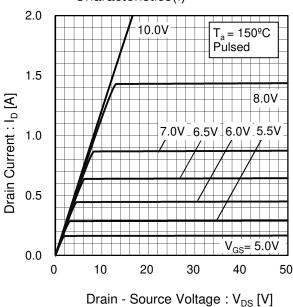
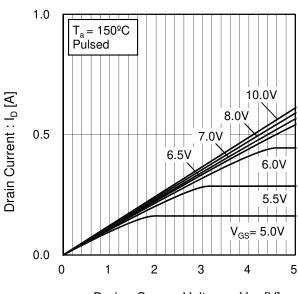
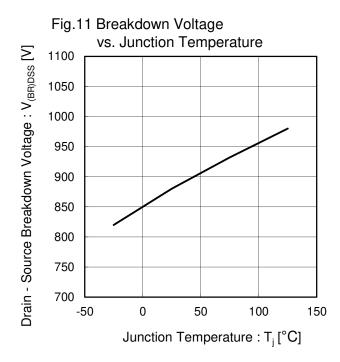


Fig.10 T_j = 150°C Typical Output Characteristics(II)





 $\begin{array}{c} 10 \\ \hline V_{DS} = 10V \\ \hline Pulsed \\ \hline 1 \\ \hline T_a = 125^{\circ}C \\ \hline T_a = 75^{\circ}C \\ \hline T_a = 25^{\circ}C \\ \hline T_a = -25^{\circ}C \\ \hline \end{array}$

Gate - Source Voltage : V_{GS} [V]

Fig.14 Transconductance vs. Drain Current

Fig.12 Typical Transfer Characteristics

Fig.13 Gate Threshold Voltage
vs. Junction Temperature

6

VDS=10V
ID=1mA
Pulsed
Pulsed

3

Junction Temperature : T_i [°C]

10 $V_{DS}=10V$ Pulsed Fransconductance: gfs [S] 1 0.1 25ºC = 75ºC 0.01 125ºC 0.001 0.001 0.1 0.01 10 Drain Current: I_D [A]

Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage 10 T_a=25ºC Static Drain - Source On-State Resistance Pulsed 8 6 $I_{D} = 2.0A$ $:R_{\mathsf{DS}(\mathsf{on})}\left[\Omega \right]$ $I_{D} = 1.0A$ 4 2 0 0 10 20 30

Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature 9 Static Drain - Source On-State Resistance V_{DS} = 10V Pulsed 8 7 6 $I_D=2A$ 5 $:R_{DS(on)}\left[\Omega \right]$ 4 $I_D=1A$ 3 2 1 0 -50 0 50 100 150

Junction Temperature : T_i [ºC]

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

Gate - Source Voltage : V_{GS} [V]

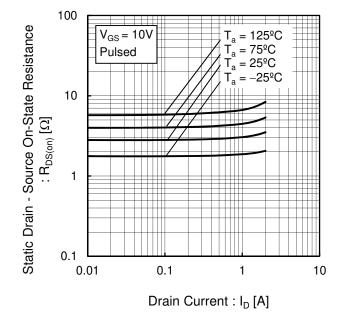
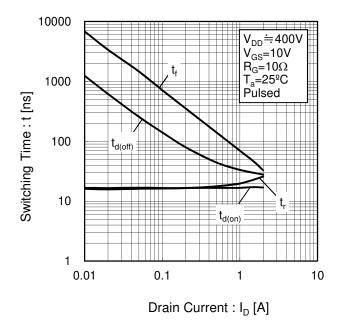


Fig.18 Typical Capacitance vs. Drain - Source Voltage 10000 T_a=25ºC f=1MHz $V_{GS}=0V$ 1000 Capacitance: C [pF] C_{iss} 100 10 C_{rss} 0.01 0.1 10 100 1000 Drain - Source Voltage : $V_{DS}\left[V\right]$

T_a = 25ºC Coss Stored Energy : $\mathsf{E}_{\mathsf{OSS}}\left[\mathsf{uJ}
ight]$ 3 2 1 0 0 200 400 600 800 Drain - Source Voltage : V_{DS} [V]

Fig.19 Coss Stored Energy

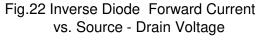
Fig.20 Switching Characteristics

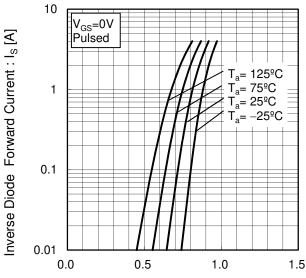


12 T_a=25ºC V_{DD}=400V 10 I_D=2A Pulsed Gate - Source Voltage : V_{GS} [V] 8 6 4 2 0 0 5 10 15 20

Fig.21 Dynamic Input Characteristics

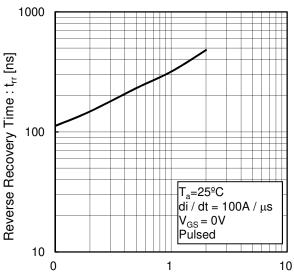
Total Gate Charge : Qq [nC]





Source - Drain Voltage : V_{SD} [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I_S [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

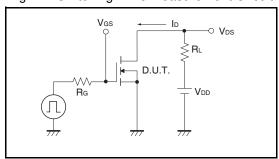


Fig.2-1 Gate Charge Measurement Circuit

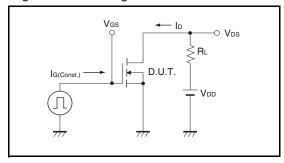


Fig.3-1 Avalanche Measurement Circuit

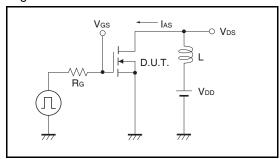


Fig.4-1 dv/dt Measurement Circuit

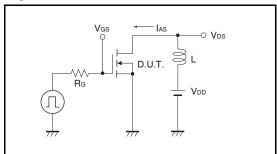


Fig.5-1 di/dt Measurement Circuit

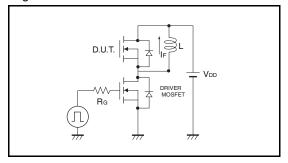


Fig.1-2 Switching Waveforms

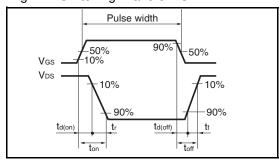


Fig.2-2 Gate Charge Waveform

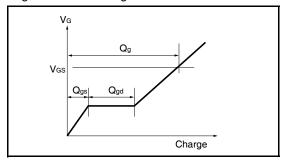


Fig.3-2 Avalanche Waveform

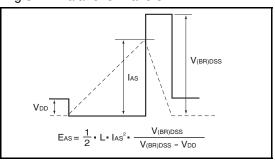


Fig.4-2 dv/dt Waveform

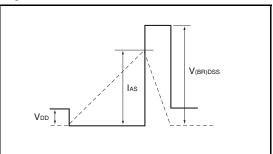
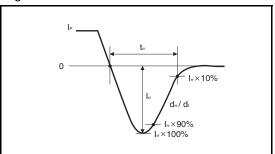
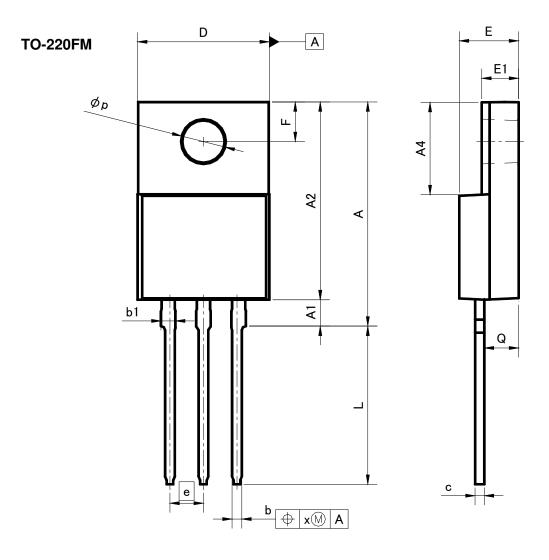


Fig.5-2 di/dt Waveform



● **Dimensions** (Unit: mm)



DIM	MILIMETERS		INC	HES
DIW	MIN	MAX	MIN	MAX
Α	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.85	0.028	0.033
b1	1.10	1.50	0.043	0.059
С	0.70	0.85	0.028	0.033
D	9.90	10.30	0.39	0.406
Е	4.40	4.80	0.173	0.189
е	2.54		0.	10
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.11	0.126
L	11.50	12.50	0.453	0.492
р	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
х	_	0.381	-	0.015

Dimension in mm/inches

Rev.003

Notice

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1. Our Products are designed and manufactured for application in ordinary electronic equipments (such as AV equipment, OA equipment, telecommunication equipment, home electronic appliances, amusement equipment, etc.). If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), transport equipment, traffic equipment, aircraft/spacecraft, nuclear power controllers, fuel controllers, car equipment including car accessories, safety devices, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JAPAN	USA	EU	CHINA
CLASSⅢ	CLASSII	CLASS II b	CLASSIII
CLASSIV		CLASSⅢ	

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 - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
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 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
 may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
 exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

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